

**AMENDMENT TO THE SPECIFICATION**

Immediately after the title, please insert the following:

**--CROSS-REFERENCE TO RELATED APPLICATIONS**

This application is a filing under 35 U.S.C 371 of International Application No. PCT/JP03/07676, filed on June 17, 2003, and published in the Japanese language. That international application claimed priority to Japanese Application No. 2002-175243, filed June 17, 2002. --

At page 8, after line 6, please add the following:

--Fig. 8A is a local longitudinal sectional view showing the main structure of the AlGaIn/GaN heterojunction Field-effect transistor in the second embodiment according to the present invention, but with an NiN layer instead of the NiSi layer of Fig. 8;--

At page 16, after line 18, insert the following:

--Fig. 8A shows a structure using a different intermetallic compound, in this case NiN. In this structure shown in Fig. 8A, an NiN layer 271a is used instead of NiSi layer 271 from Fig. 8 to form Schottky gate electrode 27a. In all other respects the structure remains the same as that shown in Fig. 8.--